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Industry's first 200W GaN HEMT is now production ready…

NITRONEX LAUNCHES NPT1007, INDUSTRY'S FIRST 200W GAN HEMT POWER TRANSISTOR

Durham, NC (January 28, 2009) - Nitronex, the global leader in gallium nitride RF power transistors, has released the NPT1007 for applications up to 1.2GHz. The NPT1007 comprises two power transistors, 100W each, in an industry standard four lead Gemini package. This small footprint allows easy combining of both transistors into a compact high power amplifier solution. After combining losses, the device achieves 200W at 63% efficiency with 18.3dB gain at 900MHz. The NPT1007 is robust to an output mismatch of 10:1 while in saturation.

"The NPT1007 was developed while working with leading power amplifier designers who needed a smaller, more efficient solution than was available on the market to date," said Ray Crampton, Director of Marketing at Nitronex. "The NPT1007 has high gain and efficiency performance from 14-28V, allowing designers to co-optimize power, thermal rise, efficiency and linearity. Success with early customers has confirmed that the NPT1007 offers a compelling solution across this voltage range."

The NPT1007 is available in a thermally enhanced ceramic air cavity bolt-down package. It is lead-free and RoHS compliant, is production ready, and is available from stock to 10 weeks lead time through Nitronex's standard sales channels.

For more information about Nitronex's 200W NPT1007 and other power transistors, visit www.nitronex.com, e-mail info@nitronex.com, or call 919-807-9100.

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About Nitronex

Nitronex is a global leader in the design and manufacture of GaN RF power devices. Based on its patented SIGANTIC® process — gallium nitride on silicon technology — Nitronex offers the performance advantages of GaN combined with the quality, reliability, and availability advantages of industry-standard silicon substrates.

Nitronex was founded in 1999 and its headquarters and wafer fabrication facilities are located in Durham, NC. It holds 19 patents with 19 others pending.

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